JFET - General Purpose Transistor

P-Channel

Features

• Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	40	Vdc
Reverse Gate–Source Voltage	V_{GSR}	40	Vdc
Forward Gate Current	I _{GF}	10	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

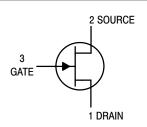
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.



ON Semiconductor®

http://onsemi.com





SOT-23 (TO-236) CASE 318 STYLE 10

MARKING DIAGRAM



M6E = Device Code
M = Date Code*

Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBF5460LT1	SOT-23	3,000 / Tape & Reel
MMBF5460LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	·		-		
Gate–Source Breakdown Voltage $(I_G = 10 \mu Adc, V_{DS} = 0)$	V _(BR) GSS	40	_	_	Vdc
Gate Reverse Current $(V_{GS} = 20 \text{ Vdc}, V_{DS} = 0)$ $(V_{GS} = 20 \text{ Vdc}, V_{DS} = 0, T_A = 100^{\circ}\text{C})$	I _{GSS}	- -	- -	5.0 1.0	nAdc μAdc
Gate Source Cutoff Voltage (V_{DS} = 15 Vdc, I_{D} = 1.0 μ Adc)	$V_{GS(off)}$	0.75	_	6.0	Vdc
Gate Source Voltage $(V_{DS} = 15 \text{ Vdc}, I_D = 0.1 \text{ mAdc})$	V _{GS}	0.5	-	4.0	Vdc
ON CHARACTERISTICS	<u>.</u>				
Zero-Gate-Voltage Drain Current $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0)$	I _{DSS}	-1.0	_	-5.0	mAdc
SMALL-SIGNAL CHARACTERISTICS	<u>.</u>				
Forward Transfer Admittance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 kHz)	Y _{fs}	1000	_	4000	μmhos
Output Admittance $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ kHz})$	y _{os}	_	_	75	μmhos
Input Capacitance $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz})$	C _{iss}	_	5.0	7.0	pF
Reverse Transfer Capacitance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 MHz)	C _{rss}	_	1.0	2.0	pF

DRAIN CURRENT versus GATE SOURCE VOLTAGE

4.0 V_{DS} = 15 V 3.5 ID, DRAIN CURRENT (mA) 3.0 2.5 = -55°C 2.0 25°C 1.5 125°C 1.0 0.5 0 0.2 0.6 8.0 1.0 1.2 1.6 1.8 2.0 VGS, GATE-SOURCE VOLTAGE (VOLTS)

Figure 1. V_{GS(off)} = 2.0 Volts

FORWARD TRANSFER ADMITTANCE versus DRAIN CURRENT

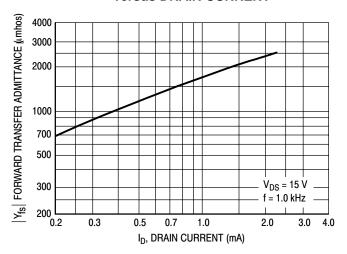


Figure 4. V_{GS(off)} = 2.0 Volts

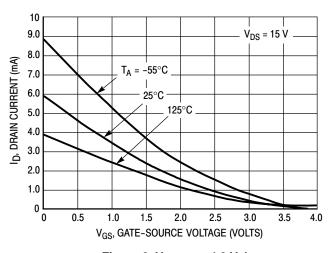


Figure 2. V_{GS(off)} = 4.0 Volts

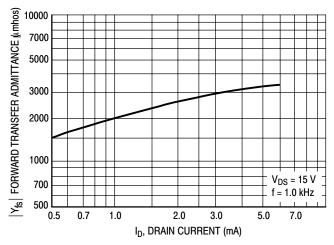


Figure 5. V_{GS(off)} = 4.0 Volts

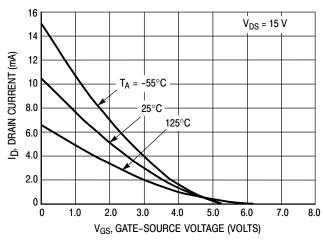


Figure 3. $V_{GS(off)} = 5.0 \text{ Volts}$

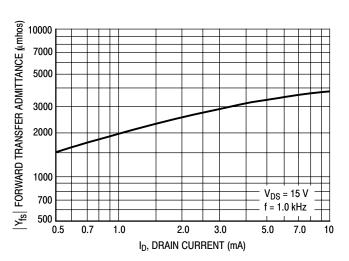


Figure 6. $V_{GS(off)} = 5.0 \text{ Volts}$

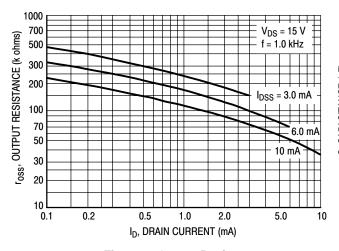


Figure 7. Output Resistance versus Drain Current

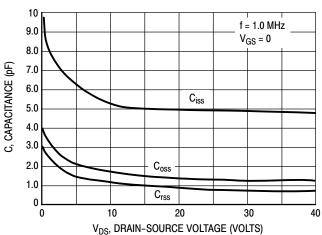


Figure 8. Capacitance versus Drain-Source Voltage

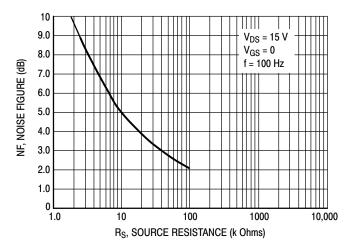
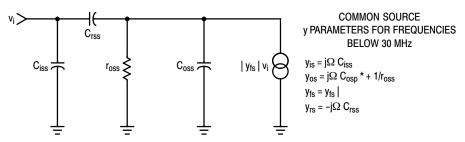


Figure 9. Noise Figure versus Source Resistance



*Cosp is Coss in parallel with Series Combination of Ciss and Crss.

NOTE:

1. Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%).

Figure 10. Equivalent Low Frequency Circuit



SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1 D - 3X b

TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	PROT	RUSIONS, OR GATE BURRS.	
--	------	-------------------------	--

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°		10°	0°		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
ANODE	SOURCE	CATHODE	CATHODE	2. DRAIN	2. GATE
CATHODE	3. GATE	CATHODE-ANODE	ANODE	3. GATE	ANODE

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
CATHODE	CATHODE	2. ANODE	CATHODE	2. ANODE	ANODE
ANODE	CATHODE	CATHODE	ANODE	CATHODE-ANOD	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
SOURCE	OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	NO CONNECTION

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
DOCUMENT N	UMBER: 98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

DESCRIPTION:

PAGE 1 OF 1

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative